

In this presentation, we will discuss how you can choose a motor driver chip for your automotive body electronics application.

Abstract

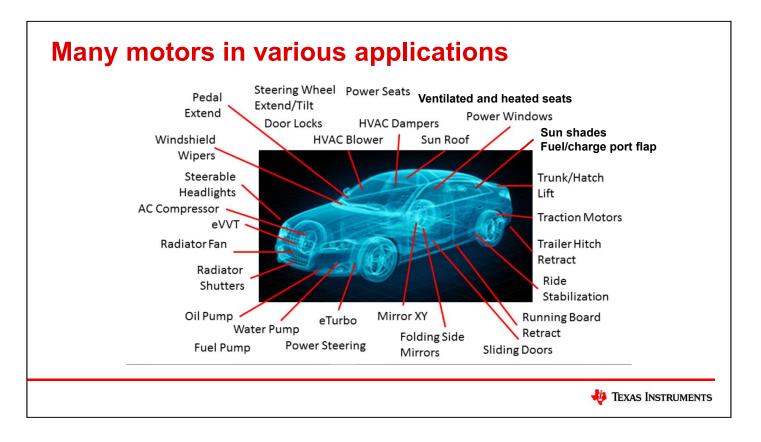
- TI offers different types of devices for driving automotive DC brushed motors
 - Single half-bridge or full-bridge motor drivers with integrated MOSFETs
 - Single half-bridge or full-bridge gate drivers for use with external MOSFETs
 - Multiple half-bridge motor drivers with integrated MOSFETs
 - Multiple half-bridge gate drivers for use with external MOSFETs
- This presentation discusses how to select which type of driver is best for different scenarios based on:
 - Number of motors
 - Motor use-case current profiles
 - Board space constraints
 - Thermal considerations
 - Current sense, diagnostics, etc.

Texas Instruments offers motor driver chips to fit just about every automotive application.

TI offers motor drivers with one half-bridge for a single motor running in only one direction, and multichannel motor drivers with up to 12 half-bridges in a single chip for multiple bi-directional motors. We also offer motor drivers with integrated MOSFETs as well as gate drivers for use with external MOSFETs, giving almost unlimited range in terms of motor current.

We will briefly discuss some of the selection criteria, such as how many motors or channels are needed, how much current is needed to drive the motor, the size of the motor driver circuit on a printed circuit board, and thermal constraints.

🐌 Texas Instruments



Various types and sizes of electric motors are found throughout an automobile. DC brushed motors are commonly used in many automotive body applications due to their simplicity and cost-effectiveness. While every application is different, we can give some general guidance on selecting the right integrated circuit to best match the requirements.

Application	Uni- or bi- directional	Operation time (seconds)	Maximum current	Normal Current
Window	bi	5	30A	5A
Lock	bi	1	10A	2A
Seat	bi	10	20A	4A
Back hatch	bi	10	10A	3A
HVAC dampers	bi	3	2A	0.5A
Mirror fold	bi	3	10A	1A
Mirror x/y	bi	5	1A	0.2A
HVAC blower	uni	continuous	10A	2A
Wiper	uni	continuous	30A	10A

This partial list of typical body motor applications shows the wide variation in requirements. Most applications require the motor to drive in two directions, but a few, such as cabin blower fans or windshield wipers, only need motor rotation in one direction. The operation time, which affects thermal calculations, can range from very short-duration such as door locks, to continuous operation for hours. The normal and maximum current levels can also vary widely, and that can have a strong influence on the selection of motor driver IC.



First let's look at motor current as one way of deciding which motor driver IC to choose.

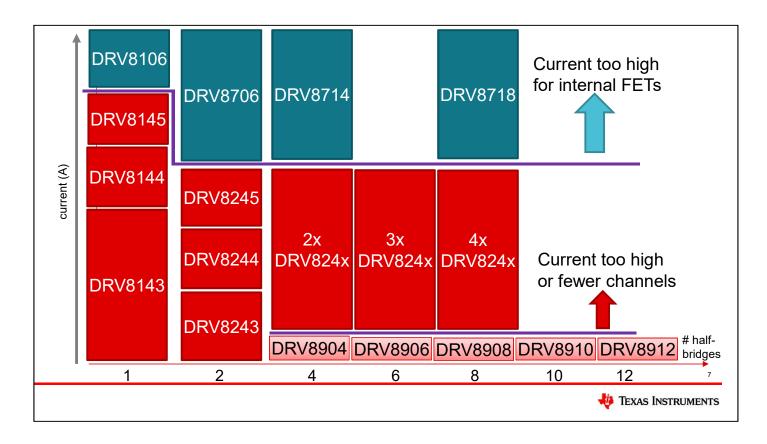
Device (DRVQ1)	Туре	Maximum Current (A)
8105, 8106	1 half-bridge gate driver	high (external FETs)
8705, 8706	2 half-bridge gate driver	high (external FETs)
8714, 8718	4 or 8 half-bridge gate driver	high (external FETs)
8145	1 half-bridge motor driver	46
8144	1 half-bridge motor driver	30
8143	1 half-bridge motor driver	20
8245	2 half-bridge motor driver	32
8244	2 half-bridge motor driver	21
8243	2 half-bridge motor driver	12
8873, 8874, 8876	2 half-bridge motor driver	3.5 to 10
89xx	4~12 half-bridge motor driver	1

This table summarizes some of the popular automotive drivers for brushed DC motors.

The top blue rows are gate driver devices, which use external MOSFETs but otherwise integrate all the features needed to drive high-current motors. The maximum current they can drive is limited only by the characteristics of the external FETs.

The middle red rows are motor drivers with integrated MOSFETs, with a wide range of maximum current capability. These are offered as either single half-bridges, or full-bridge (two half-bridge) devices.

The bottom pink row is a family of multiple half-bridge drivers with integrated FETs. These devices are well suited for applications where several channels of relatively low current are needed.

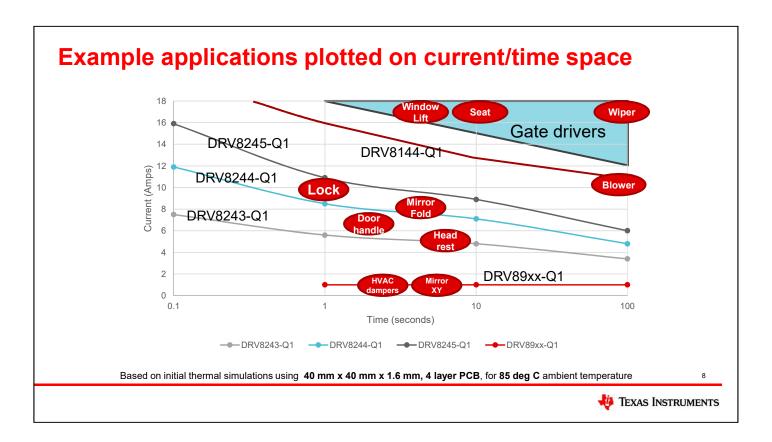


Another way to look at TI's brushed DC motor drivers is by the number of channels as well as current levels.

For low-current applications needing several half-bridges, the DRV8904-Q1 through DRV8912-Q1 are a good fit.

For single and dual half-bridges with medium current, the DRV81xx and DRV82xx-Q1 devices should be the first choice.

For high current applications, gate driver devices with external FETs should be used.



Here various applications are plotted with the current-versus-time curves for some of the motor drivers.

Lock motors typically operate for a second or less, and might have maximum currents up to 10 amps. The DRV8245-Q1 might be a good fit.

A power headrest could be adjusted for a few seconds with a current of about 5 amps. A DRV8243-Q1 would be a candidate.

The mirror fold motor could use a DRV8244-Q1 or DRV8245-Q1 to drive up to 10 amps for a few seconds.

Pop-out door handles with a maximum current of about 8 amps could select the DRV8244-Q1.

Lower-current motors for the ventilation dampers and side mirror adjustments could use a DRV89xx-Q1, with up to 12 half-bridges in one package.

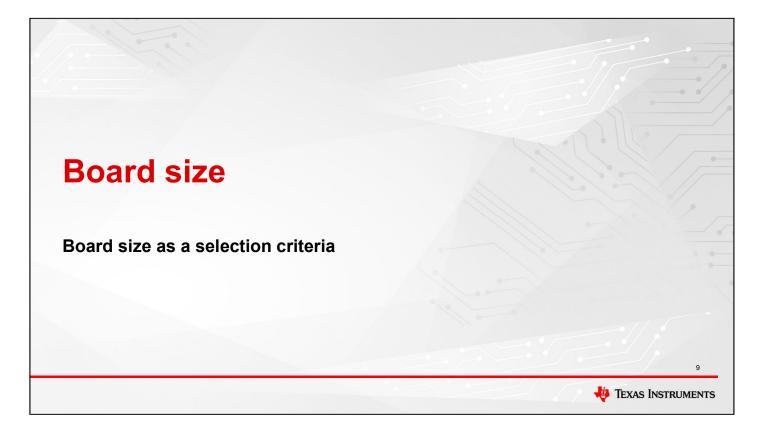
Window lift motors can have currents well above 10 amps, so a gate driver with external FETs is a good choice.

There may be several seat motors with high current in each seat, so a multi-channel gate driver like the DRV8714-Q1 or DRV8718-Q1 is a good choice.

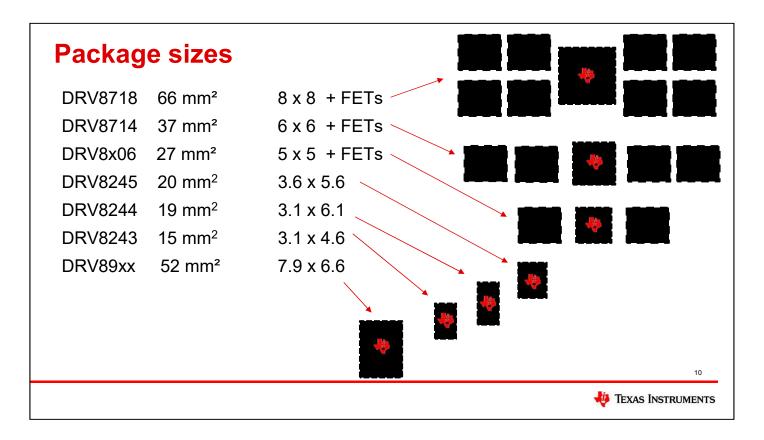
So far all of these applications have been bi-directional, but some motors only need to turn in one direction.

Windshield wiper motors are typically uni-directional, and rely on mechanical arrangement to turn the rotary motion into wiper motion. Due to their high current and long-duration operation, a gate driver with external FETis probably needed.

Similarly the cabin ventilation blower runs in one direction, and can run continuously. Depending on the current, a DRV8144-Q1 might be a candidate. Some blowers use brushless motors rather than brushed motors; for these look at TI's BLDC motor drivers.



In many applications, board size is a significant constraint. Let's look at how the different choices compare in terms of area on the printed circuit board.



The DRV8718-Q1 and external FETs provide eight channels of high-current half-bridge drives. This view shows the relative sizes of the gate driver chip and eight dual-FET packages. This arrangement can drive four independent bi-directional motors, or up to seven motors with some constraints on simultaneous operation.

The DRV8714-Q1 and external FETs provide four channels of high-current half-bridge drives. This can drive two independent motors or up to 4 single-direction motors.

The DRV8706-Q1 with external FETs provides two channels of high-current half-bridge drives. This can drive one bi-directional high-current motor or two uni-directional motors.

The DRV8245-Q1 includes integrated drive FETs to control a bi-directional motor with a maximum current of 32 amps.

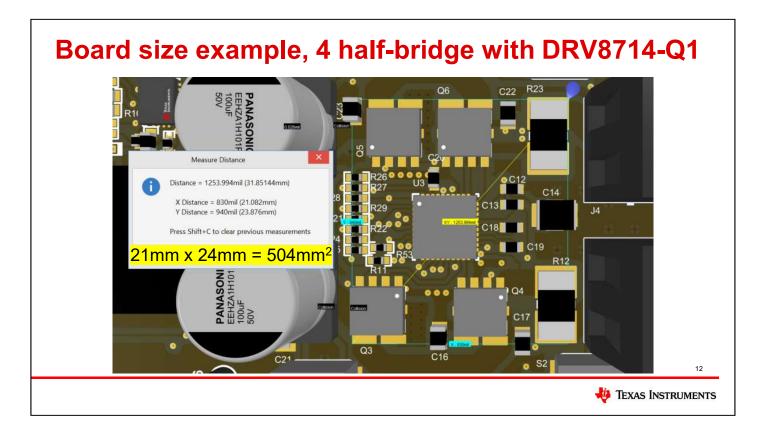
The DRV8244-Q1 can drive a bi-directional motor with a maximum of 21 amps.

The DRV8243-Q1 can drive a bi-directional motor with a maximum of 12 amps.

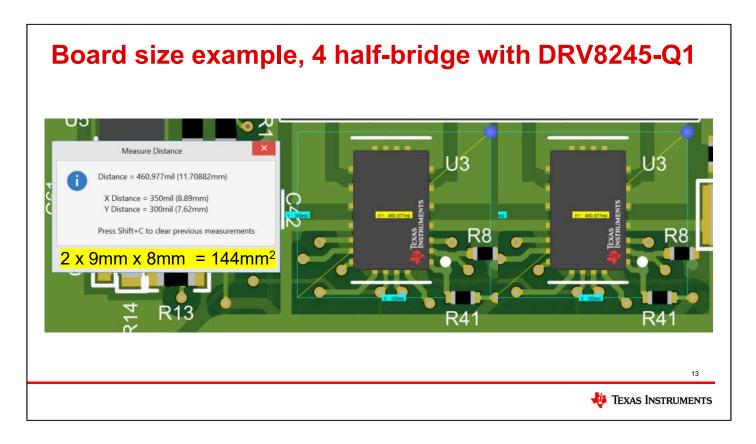
The DRV89xx-Q1 family of devices has 4, 6, 8, 10 or 12 half-bridges to drive multiple motors and loads with current up to 1 amp on each half-bridge output.

4 half-bridg	es with	2 current sen	se	
• DRV8714	37mm ²	DRV8245 HTSSOP	65mm ²	in HR 20 mm ²
• 8 FETs	140mm ²	DRV8245 HTSSOP	65mm ²	in HR 20 mm ²
 <u>2 sense resisto</u> 	rs 62mm ²			
 Sub-total 	239 mm ²		130 mm²	40 mm ²
This does NOT	include pass	ive components or pa	art-to-part :	spacing
				👋 Texas Instruments

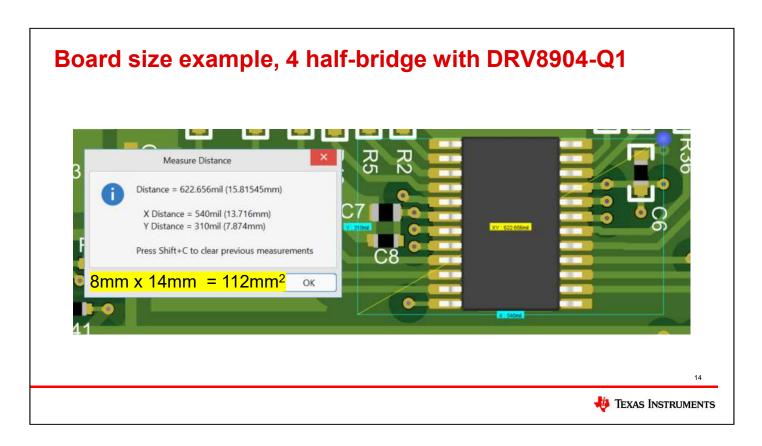
If we consider just the package sizes, we can compare the area for either the gate driver with external FETs, or the integrated FET motor drivers. In the case where four half-bridges are needed, two of the DRV8245-Q1 devices in either the HTSSOP or Hotrod package are significantly smaller than using a gate driver solution. The gate driver with external FETs can be designed for very high currents, but if the current specifications of the integrated FET devices are sufficient, these have a clear size advantage.



In this example, the DRV8714-Q1 gate driver is shown along with four dual-FET packages, plus two 3 Watt current sense resistors, and all the passive components to implement a four high-current halfbridge design. This could be used to drive two independent window lift motors, or three high-current seat motors with some constraints on their simultaneous motion.



Here we see two DRV8245-Q1 devices next to each other with the associated passive components included. This also implements a four half-bridge design, but for typically lower currents than the gate driver design. For applications where the current matches the specifications for these devices, a very compact solution is achieved.



For low-current motors such as mirror XY adjustment and ventilation dampers, the multi-channel DRV8904-Q1 provides an even more compact design. For load currents up to 1 amp per output, as many as 12 half-bridges are available in this same package size.



When driving motor loads, thermal considerations can also be of high importance. Thermal issues are related to package size and current levels, with additional constraints and tradeoffs.

DRV871x-Q1 – not a significant heat source

		DRV8718-Q1	DRV8714-Q1	DRV8714-Q1		
	THERMAL METRIC ⁽¹⁾	RVJ (VQFN)	RVJ (VQFN)	RHA (VQFN)	UNIT	
		56 PINS	56 PINs	40 PINS		
R _{0JA}	Junction-to-ambient thermal resistance	25.6	24.7	31	°C/W	
R _{0JC(top)}	Junction-to-case (top) thermal resistance	15.2	14.1	20.9	°C/W	
R _{0JB}	Junction-to-board thermal resistance	10.0	9.0	12.5	°C/W	
Ψ _{JT}	Junction-to-top characterization parameter	0.2	0.2	0.2	°C/W	
Ψ _{JB}	Junction-to-board characterization parameter	9.9	9.0	12.4	°C/W	
R _{0JC(bot)}	Junction-to-case (bottom) thermal resistance	3.0	2.3	2.3	°C/W	
		-			_	
		FET	FET	FET	FET	
		FET	FET	FET	FET	

In general, high-current applications using gate drivers such as the DRV8706-Q1 or DRV8718-Q1 don't have thermal issues with the gate driver device itself. This is because the high motor current flows through the external FETs rather than the gate driver.

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	nol 60 V (D_S)	175 °C MO	SEET	Features OptiMOS™ - power MOSFET for a	automotive	applications	PG-TDSON	4-8-33
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The external MOSFETs used with TI's gate drivers are available with a wide range of on resistance, in a variety of packages. Many automotive FETs are rated for operation with junction temperature up to 175 centigrade. In a high-current application, this can be an advantage in terms of thermal performance. The packages typically have large metal heat slugs to aid in transferring heat away from the transistor and into the printed circuit board. This leads to a relatively low thermal resistance from junction to ambient, known as theta JA.

DRV8245-Q1 thermal specifications

7.4 Thermal Information

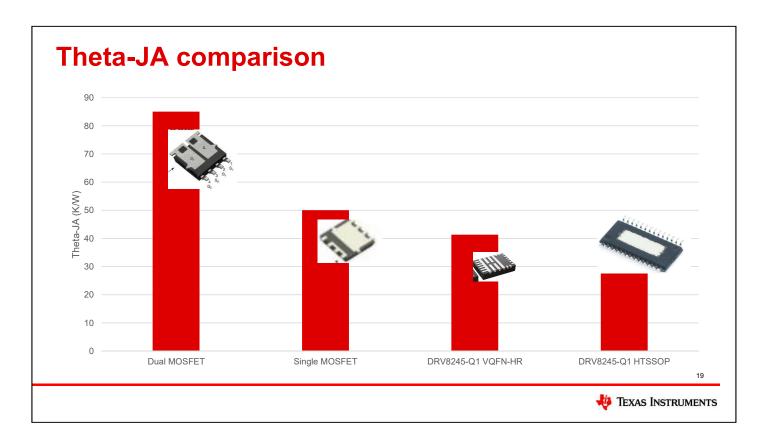
Refer Transient thermal impedance table for application related use case.

	THERMAL METRIC ⁽¹⁾	HTSSOP package	VQFN-HR package	UNIT
R _{8JA}	Junction-to-ambient thermal resistance	27.7	41.3	°C/W
R _{0JC(top)}	Junction-to-case(top) thermal resistance	13.8	14.4	°C/W
R _{0JB}	Junction-to-board thermal resistance	7.1	5.5	°C/W
Ψ _{JT}	Junction-to-top characterization parameter	0.6	0.3	°C/W
Ψ _{JB}	Junction-to-board characterization parameter	7.1	5.4	°C/W
R _{8JC(bot)}	Junction-to-case(bottom) thermal resistance	0.9	N/A	°C/W

7.5.5 Power FET Parameters

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
	High-side FET on resistance, HTSSOP	I _{OUT} = 6 A, T _J = 25°C		20		mΩ
D	package	I _{OUT} = 6 A, T _J = 150°C			38	mΩ
R _{HS_ON}	High-side FET on resistance, VQFN-HR	I _{OUT} = 6 A, T _J = 25°C		16		mΩ
	package	I _{OUT} = 6 A, T _J = 150°C			30.4	mΩ
	Low-side FET on resistance, HTSSOP	I _{OUT} = 6 A, T _J = 25°C		20		mΩ
P	package	I _{OUT} = 6 A, T _J = 150°C			38	mΩ
R _{LS_ON}	Low-side FET on resistance, VQFN-HR	I _{OUT} = 6 A, T _J = 25°C		16		mΩ
	package	I _{OUT} = 6 A, T _J = 150°C			30.4	mΩ

The innovative packaging of the DRV8243, 44, and 45-Q1 devices give them even lower theta JA values than the external FETs, which is a significant advantage in terms of power dissipation in a small package.

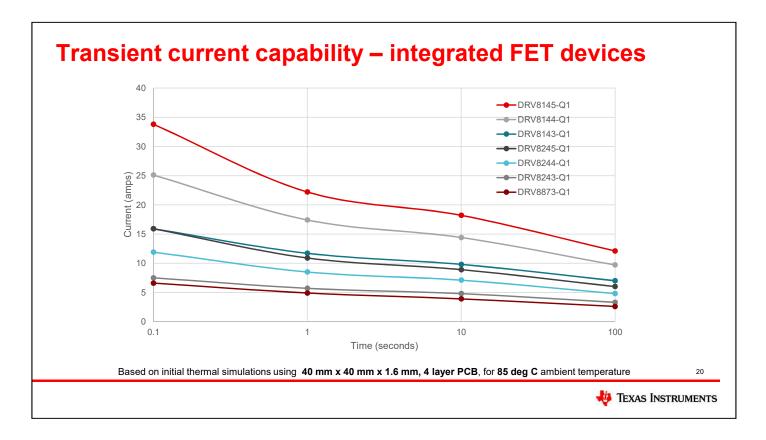


The parameter of thermal resistance from integrated circuit junction to ambient temperature (theta JA) can be used to compare the thermal efficiency of various devices.

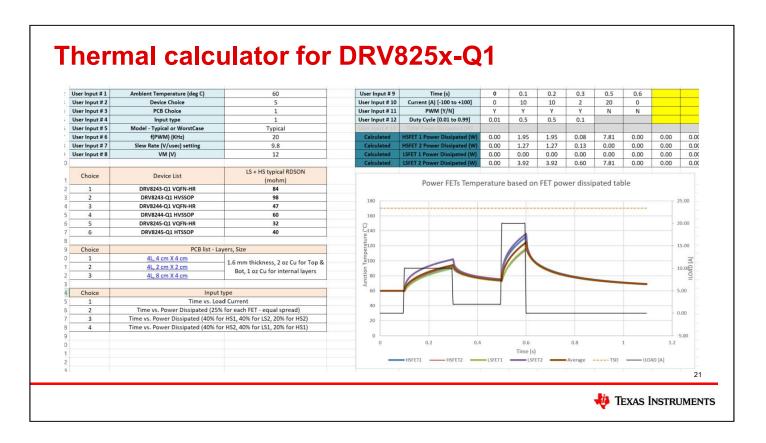
The dual MOSFETs in a 5 by 6 mm package have a thermal resistance of 85 degrees per Watt, while the single MOSFETs in a similar package have a lower thermal resistance, due to the larger continuous thermal slug.

The DRV8245-Q1, in a small 3.6 x 5.6 mm package, has lower thermal resistance due to the "hot-rod" flip chip packaging technology.

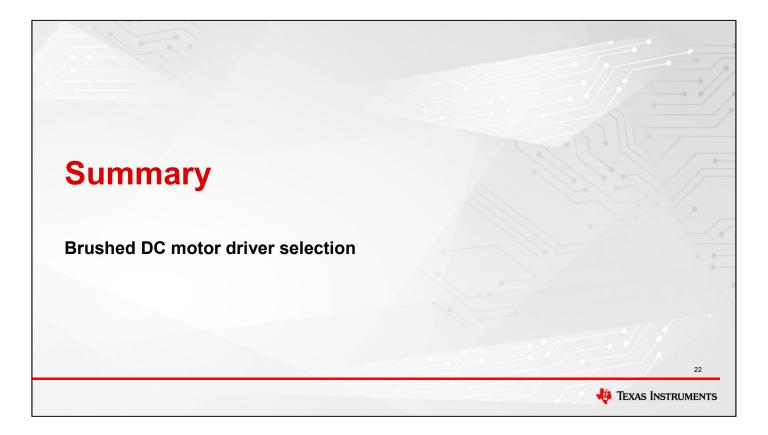
The DRV8245-Q1 in the HTSSOP package is somewhat larger, but has an even lower thermal resistance than the VQFN hotrod package.



The thermal constraints of integrated circuits are based on internal power level and duration. TI motor drivers typically are specified for operation up to 150 degrees centigrade at the integrated circuit junction, and have thermal protection features in case that junction temperature is exceeded due to application fault conditions. External factors such as board design and ambient temperature also affect thermal calculations. In general, high currents are possible for a short duration, and longer durations with lower currents are also fine.



On the product page for the DRV8245-Q1, and other devices in this family, you can find a thermal calculator that estimates the internal junction temperature based on several factors, including the current profile and type and size of printed circuit board. Use this calculator to see which of the devices is the best fit for your specific application.



Let's wrap up with a review of what we've discussed.

Brushed DC motor drivers comparison

Feature	Single multiple-channel gate driver (+ externalFETs) DRV871x-Q1	Multiple single-channel motor drivers (internal FETs) DRV824x-Q1	Multiple-channel motor drivers (with internal FETs) DRV89xx-Q1
Max current per motor	50A+ (FET limited)	Up to 32A (DRV824x)	1A
Devices for 2	1 DRV8714 + 8 FETs	2 DRV8245	1 DRV8904
independent motors Devices for 4 independent motors	(or 4 dual FETs) 1 DRV8718 + 16 FETs (or 8 dual FETs)	4 DRV8245	1 DRV8908
Board space per motor	Medium	Small	Very small
Current sense	2 integrated CSA, external shunt resistors required	Integrated current mirror per motor	Integrated overcurrent detection
Interface	SPI plus parallel for PWM	SPI plus parallel for PWM	SPI
Power off braking	Yes	No	No
Integrated diagnostic and protection	Yes	Yes	Yes
Adjustable slew rate	Yes	Yes	No
External CP caps	Yes	No	No
PWM	Yes, from external source	Yes, from external source	Yes, internal up to 2 kHz

In summary, designers can select from a broad range of motor driver solutions to meet the needs of just about any application. While we have discussed some of the main criteria for choosing between the various devices available from Texas Instruments, there are other reasons why one device or another may be the best fit. For example, the method and precision of current measurement for system feedback, or type of interface between the motor driver and microcontroller may be a key consideration in some designs. Other features such as diagnostic and protection against fault conditions, built-in braking, adjustable voltage slew rate during pulse-width modulation, or availability of a charge pump voltage might be valuable in specific applications.

Overall, motor drivers from Texas Instruments fit the needs of designers for all types of automotive designs.

